

Energy response of MAPS designed at C4PI

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On behalf of the C4PI

Energy measurement @ C4PI



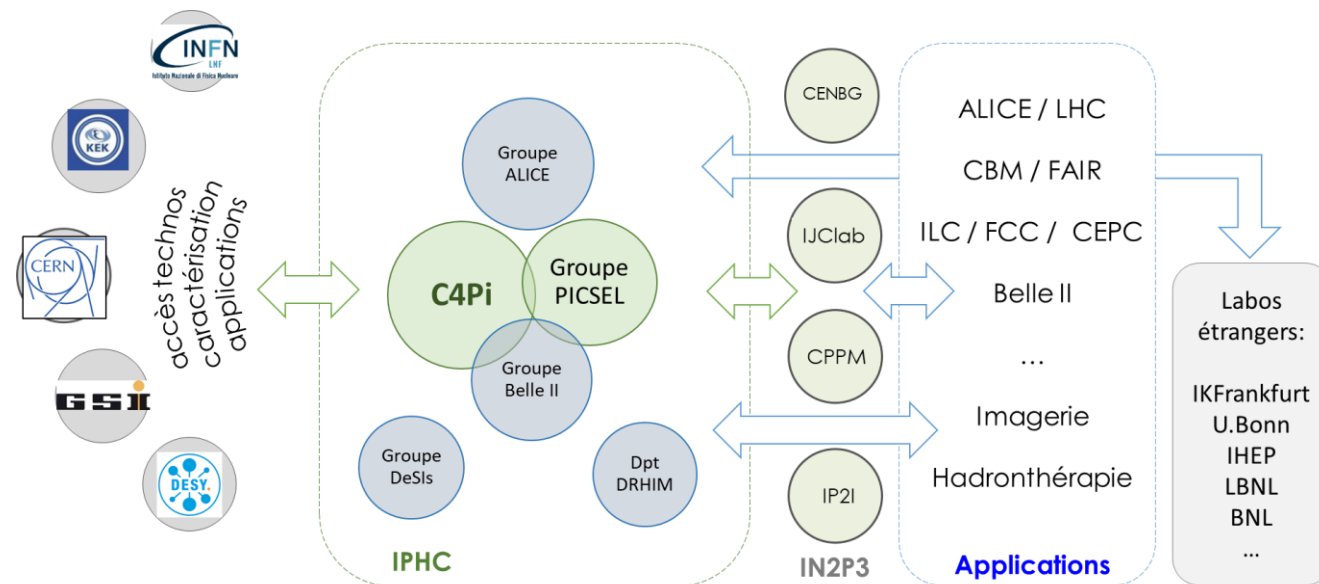
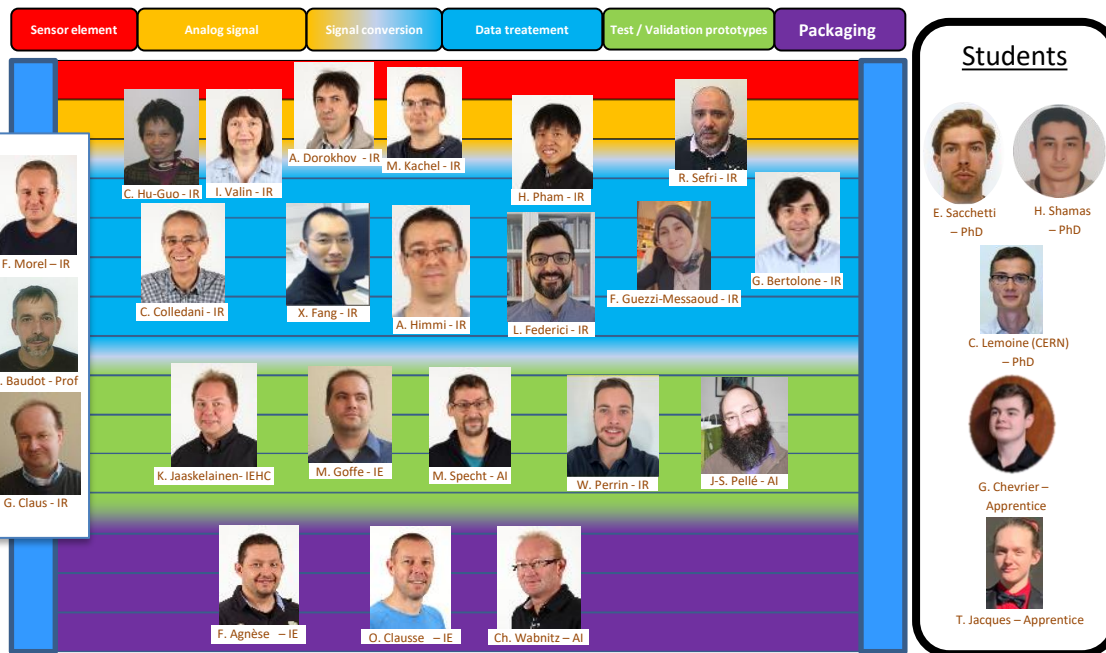
1. Main HEP applications



2. Spectroscopy



3. Ion identification



Our Goal: Provide sensors for HEP applications

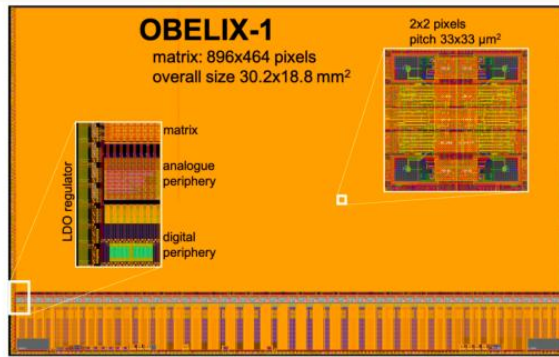
1. Energy measurement in HEP applications

■ Why sensors for trackers needs to measure energy

- Correct time walk
- Better spatial resolution

OBELIX-1

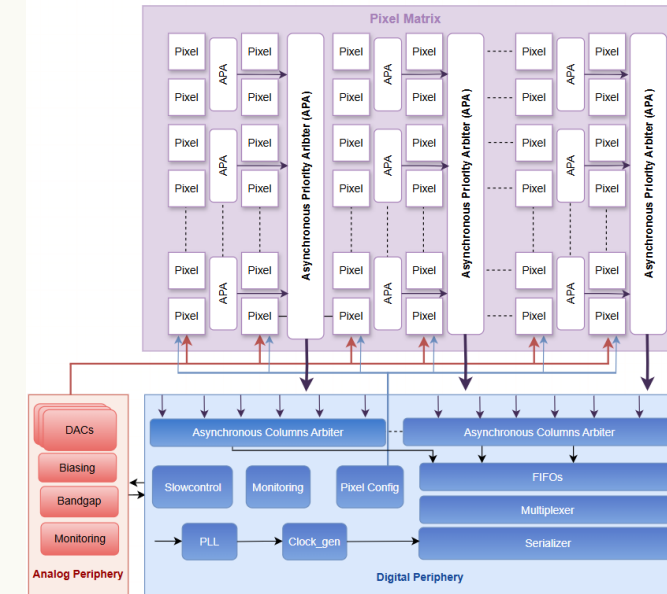
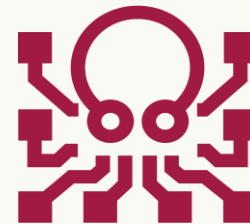
BELLE II VTX Upgrade



- BELLE II VTX collaboration
- 7-bit TOT in pixel
- Time-walk compatible with 25 ns 98% in-time efficiency

[10.1016/j.nima.2023.168015](https://doi.org/10.1016/j.nima.2023.168015)

OCTOPUS DRD3 collaboration

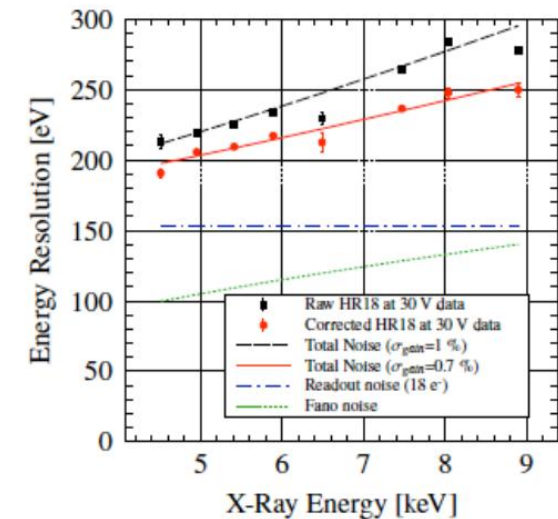
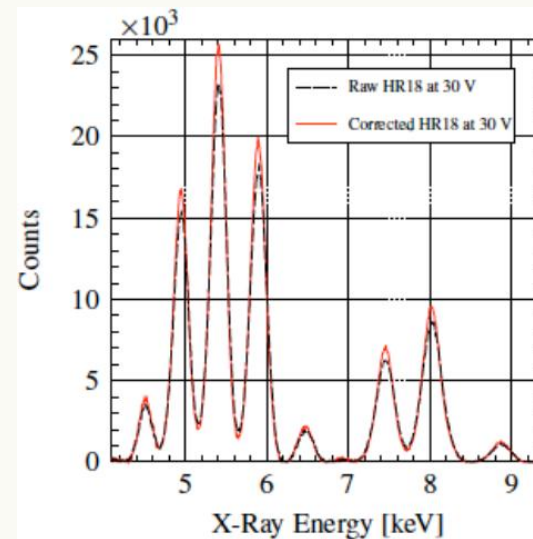


Aims to reach 3 μ m spatial resolution => TOT for time walk correction & cluster center calc.

New MAPS technologies made it better:

-
- The diagram illustrates the structure and carrier transport in a SiC MOSFET. The top layer is the gate stack, followed by a p-type substrate. The channel region is defined by an N-well (N+) and a p-type well (P+). The source and drain regions are p-type (P+). The substrate is a deep p-well (DEEP P-WELL). The carrier transport is shown with electrons (e-) moving from the source to the drain under the influence of an electric field (E). The carrier transport is labeled with $h\nu_2$ and $h\nu_1$, indicating the energy levels of the carriers.

- Prototype chip 32x128 pixels
- Analog outputs
- Pixel size 22 x 22 μm^2
- **Small (4 μm) circular diode**
- **AC coupled** collecting diode
- Produced on two substrates:
 - Epitaxial layer 18 μm
 - High resistivity substrate



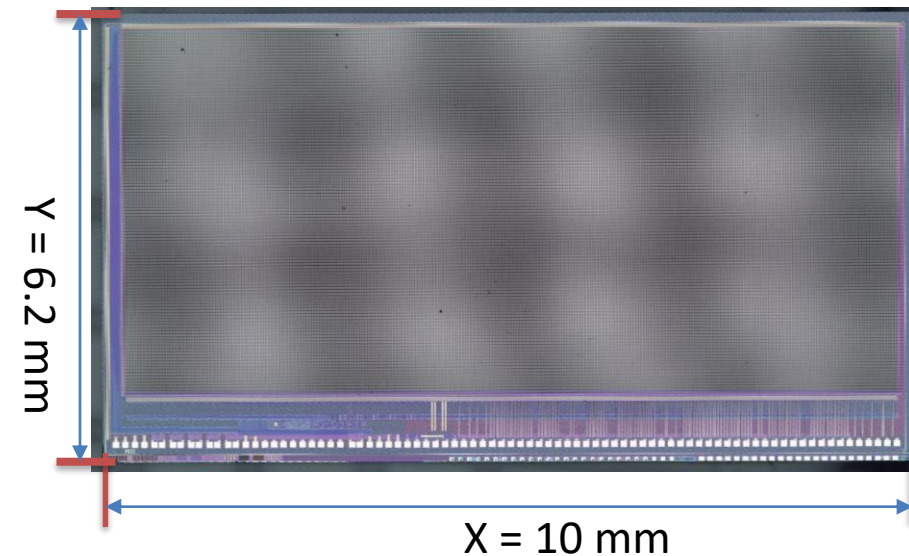
PhD thesis of Julian Heymes

Maciej Kachel

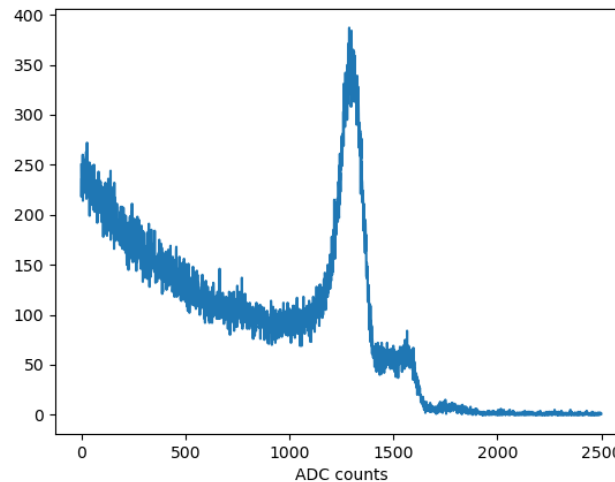
2b. Spectroscopy – application circuit

Monolithic Imager 1 :

- DC coupled pixels with diode reset
- Back biasing (TJ modified process)
- Pixel size 20x20 μm
- Matrix of 256x512 pixels
- Rolling/global shutter operation
- Programmable analog readout

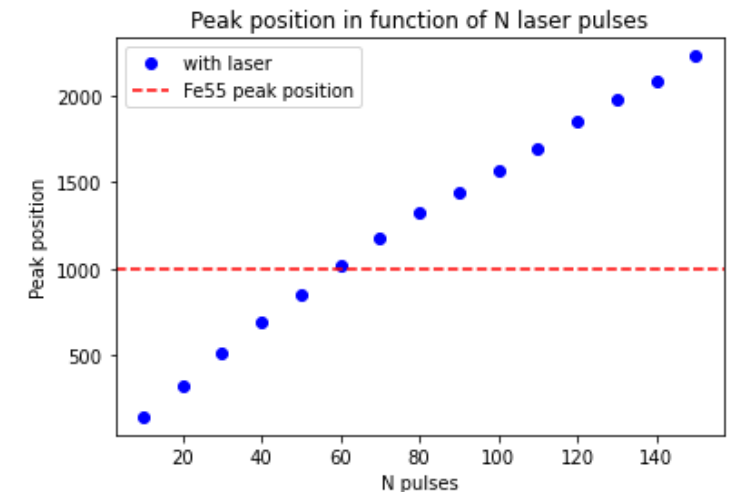
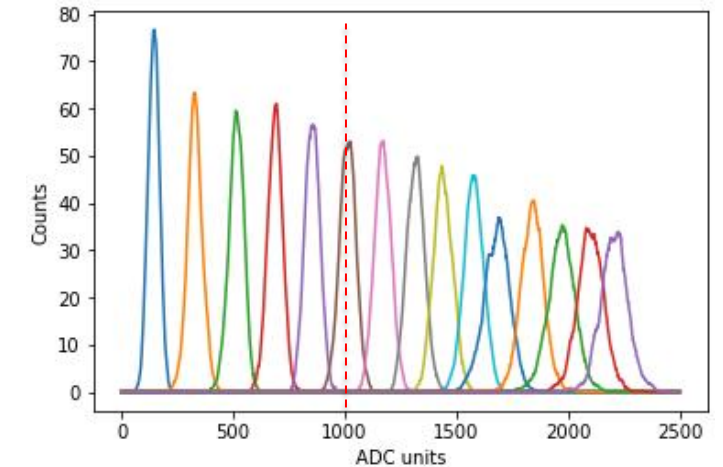


Energy resolution



- Front side illumination @ room T
- No correction
- Energy resolution ~ 350 eV

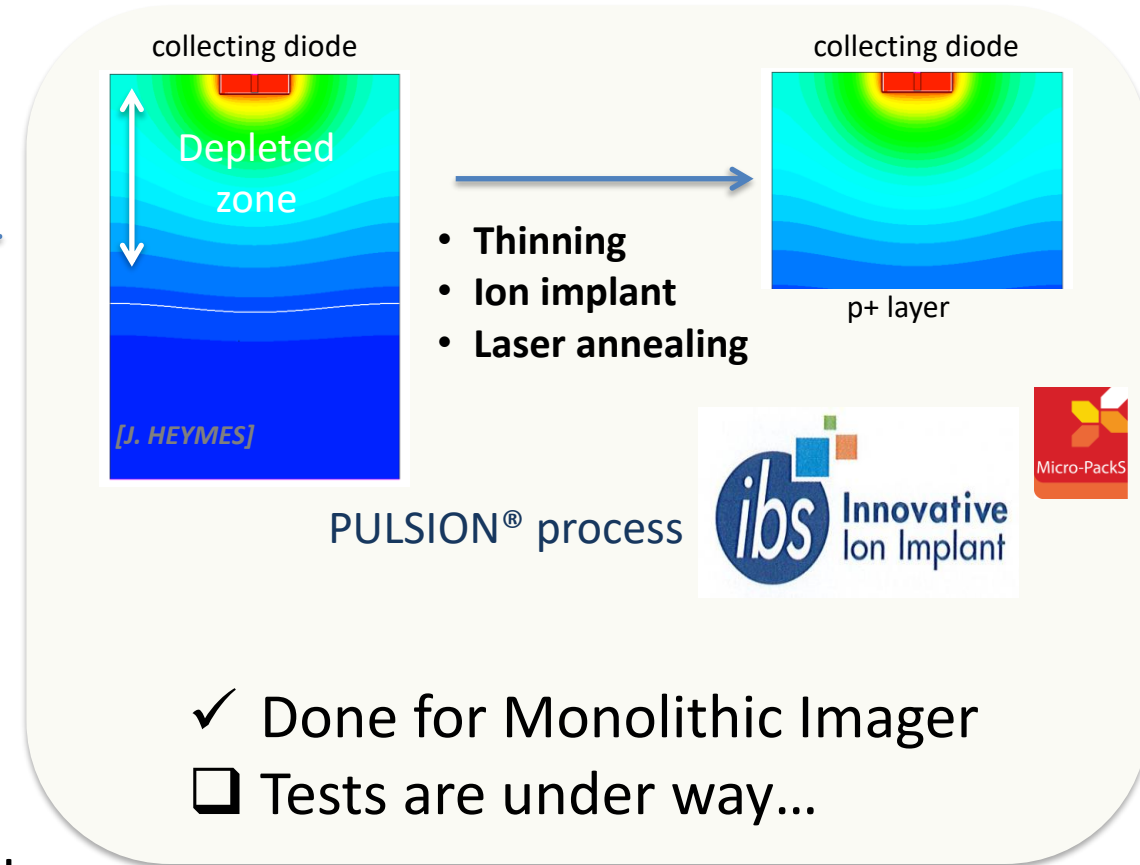
Dynamics (NIR laser)



2c. Spectroscopy – How to make it better

- Enable low E (<1keV) particles measurement
- Higher Quantum efficiency => Full depletion
 - Mix of modified process, thick epi (or Czochralski substrate) and **back side processing**
- Better energy resolution
 - In-pixel gain => APIX project @ C4PI
- High frame rate
 - ADC on chip => 12bit column ADC developed with collaboration between LPSC, APC& IPHC

Sensor post processing



3a. Ion identification – “historical” example

MAPS can be useful for Ion identification => Gaussian like distribution unlike the high energy particles – Landau

Mimosa28 (Ultimate)

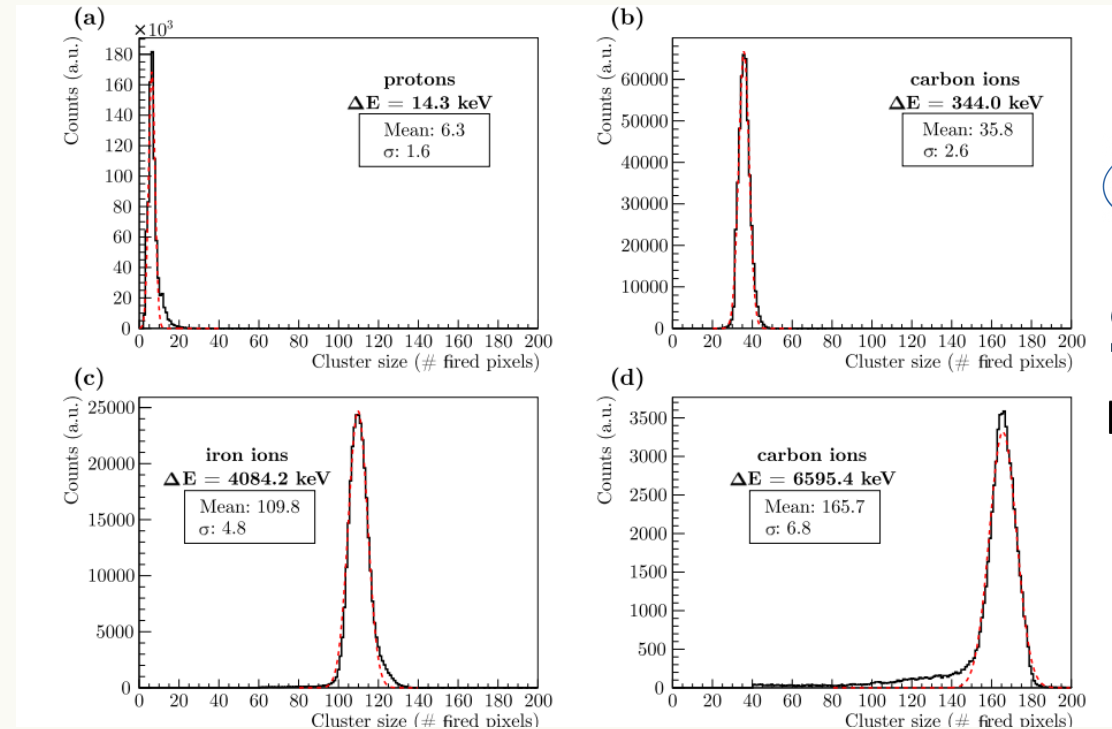
- Matrix: 928 x 960
- Pixel pitch: 20.7 μm
- AMS 0.35 high-res process
- Readout time= 185.6 μs
- Rolling Shutter readout



PXL, STAR
experiment at
BNL



First vertex detector at a collider experiment based on MAPS



C.-A. Reidel et al, “Response of the Mimosa-28 pixel sensor to a wide range of ion species and energies” NIMA, vol. 1017 (2021) 165807 - <https://doi.org/10.1016/j.nima.2021.165807>

Indirect energy measurement via cluster size

3b. Ion identification – TIIMM project

TIIMM
target =

Precision tracking
 $\sigma_{\text{pos.}} \leq 10 \mu\text{m}$

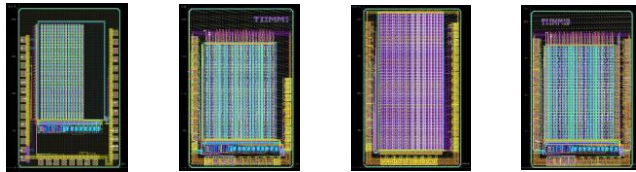
+

Low material budget $\ll \%$
 X_0

+

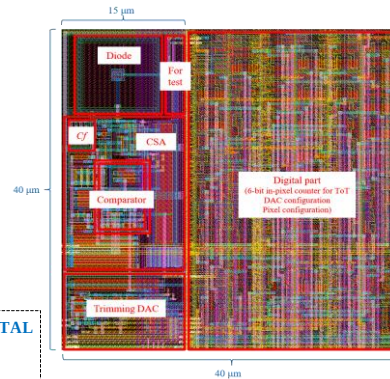
Energy loss measurement
 $1-10^3 \text{ MIPs}$

Family of TIIMM sensors was designed (2020-2023)

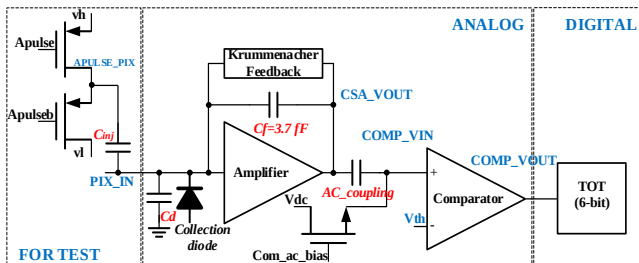


Goal: Linearity up to 800 ke⁻

- Krummenacher feedback
- AC coupled comparator
- 6-bit TOT
- ~40x40 μm pixel



Pixel layout

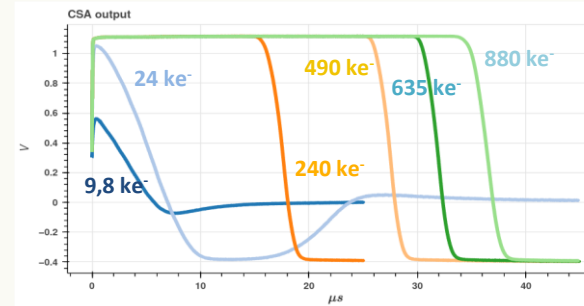


Pixel schematics

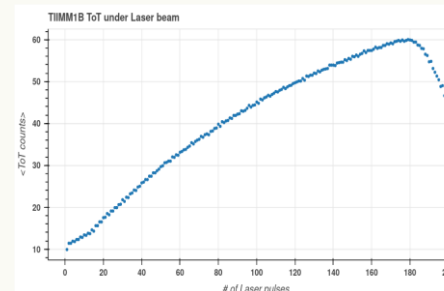
Tracking

Identification

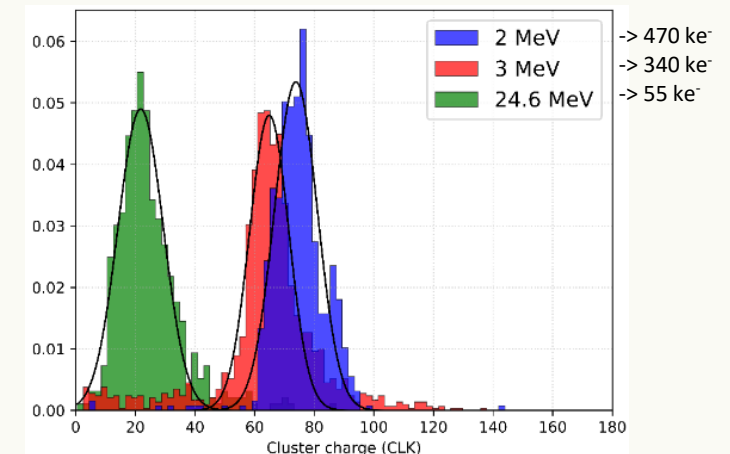
CSA output



Output linearity with laser



Proton measurements at AIFIRA (Bordeaux) and CYRCE (Strasbourg)

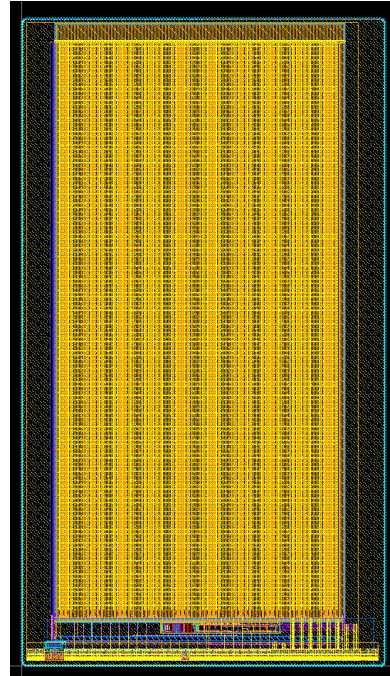


Promising results but can we do more than 6bit TOT ??

3c. Ion identification – Next steps

IMPACT sensor

- Analog front end => TI1MM1B
 - Large linearity
- Digital => TOT measurement:
 - **12bit per pixel**
 - Single hit/Accumulation counting
 - Synchronous readout
- Design for Test (masking/pulsing)
- Matrix:
 - Pixels of $50 \times 50 \mu\text{m}^2$
 - 128x64 pixels
 - Active area = $6.4 \times 3.2 \text{ mm}^2$
- 8 digital outputs @ 50MHz
=> 4k frame rate



*Submission
under way*

Next steps

- Verify the sensor functionality
- Build a multi-sensor detector

Next version goals

- Asynchronous readout
- High speed serializers
- Bigger area (few cm^2)

- Main branch of the C4PI (HEP applications)
 - OBELIX
 - OCTOPUS
 -
- Application branch of the C4PI (Spectroscopy, Ion identification)
 - Low energy X-ray / electron tests
 - In-pixel gain development
 - ADC development
 - TOT sensors development for Ion identification (IMPACT and more)

Thank you for your attention



Back-up: some generic informations

Sensor tested: TIIMM 1B (uniform N layer + extra deep P)

- Module n°10: 25 μm EPI
- Module n°13: 50 μm EPI

6 bits ToT + prescaler (CLK cycle period multiplier)

2 measurements campaigns with proton beams :

- AIFIRA (LP2iB, Bordeaux) 04.2024
2 MeV, 3 MeV
- CYRCE (IPHC, Strasbourg) 02.2025
5 MeV, 10 MeV, 15 MeV, 20 MeV

